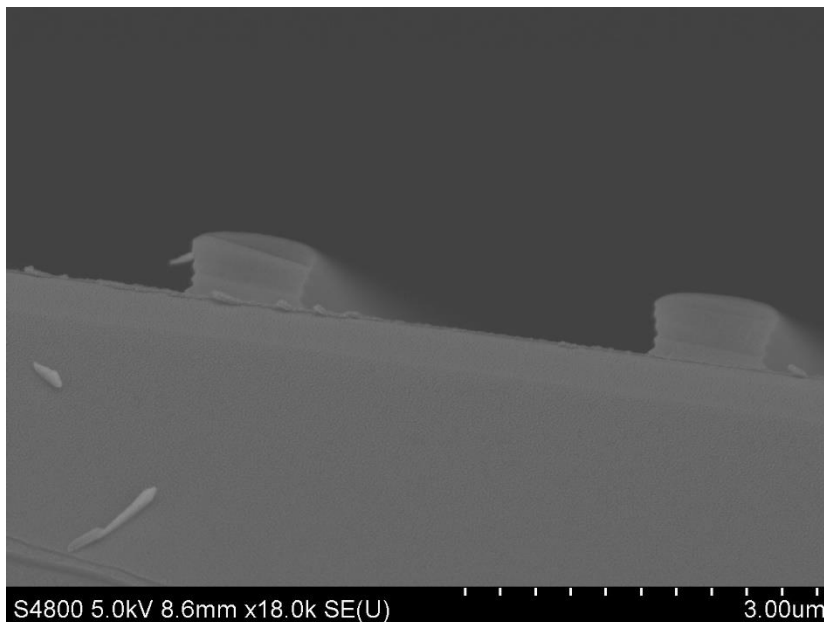


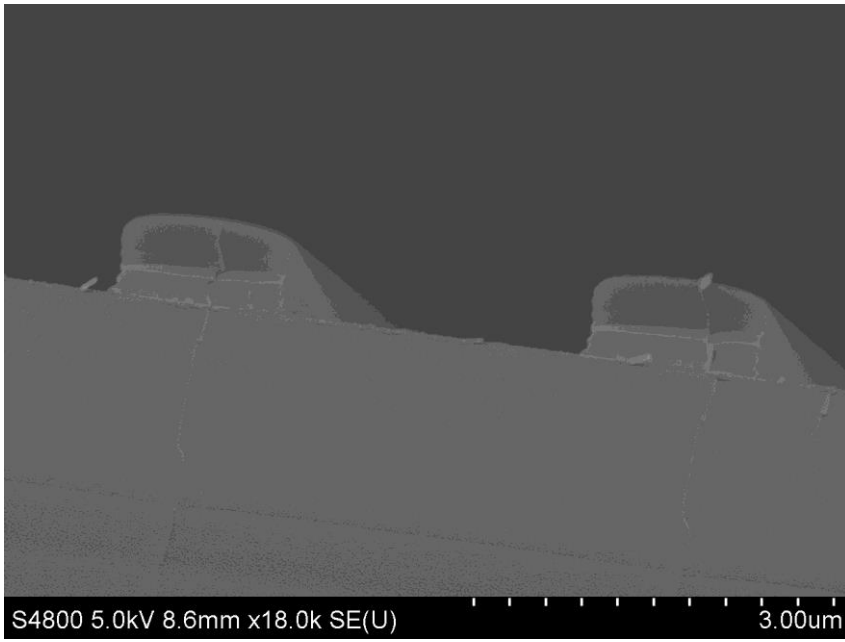
MaN-1410 tunable pattern profile: vertical to undercut (suitable mask for both lift-off and etch processes)

Tone	Negative
Substrate preparation	spincoat wafer with HMDS (@4000rpm) and bake on hotplate at 200°C for 2 minutes or use recipe 3 on the Delta RC80 for evaporation of HMDS onto the wafer at 150°C
Spincoat	0.5-2.5um @6000-2000rpm (1um @3000rpm)
Bake	at 100°C for 90s on hotplate for small pieces or @110°C for 90s in oven for 4" wafers and thick resist layers
Exposure	HBG_uMLA: D= 180mJ/cm ² (pneumatic focussing, defoc -4)
Development	MAD533 for 60s
Rinse	water

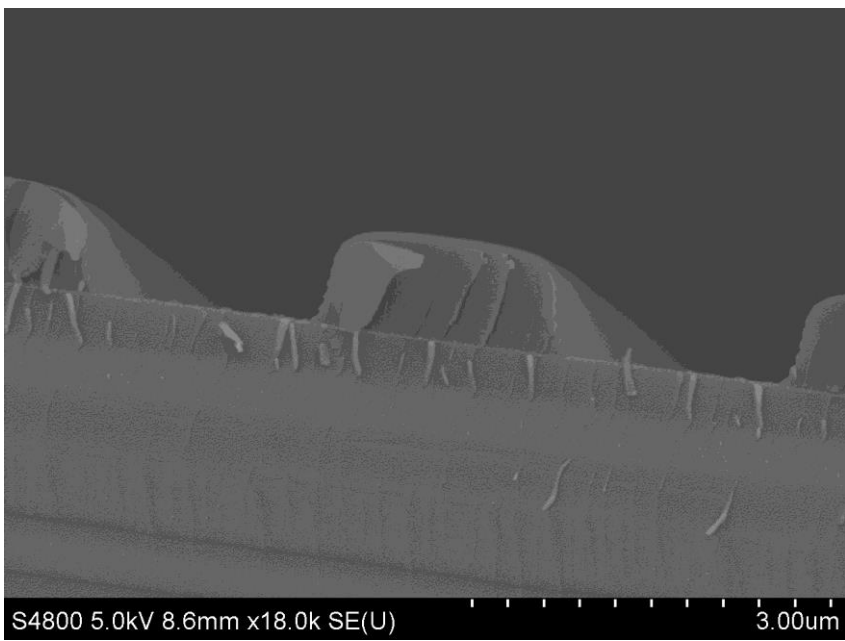
Pattern profile is depending on dose and development time.



D = 105mJ/cm²



D=135mJ/cm²



D=175mJ/cm²

D=175mJ/cm²

